

# FMP08N50E

FUJI POWER MOSFET

## Super FAP-E<sup>3</sup> series

## N-CHANNEL SILICON POWER MOSFET

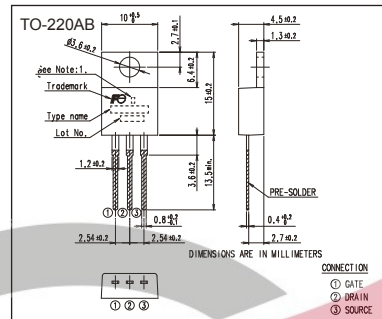
### ■ Features

- Maintains both low power loss and low noise
- Lower R<sub>DS(on)</sub> characteristic
- More controllable switching dv/dt by gate resistance
- Smaller V<sub>GS</sub> ringing waveform during switching
- Narrow band of the gate threshold voltage (3.0±0.5V)
- High avalanche durability

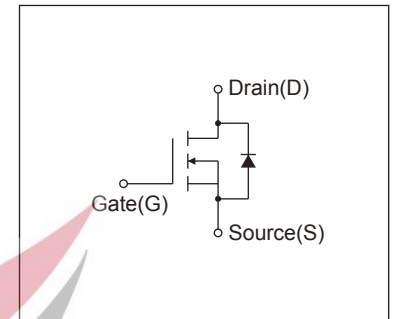
### ■ Applications

- Switching regulators
- UPS (Uninterruptible Power Supply)
- DC-DC converters

### ■ Outline Drawings [mm]



### ■ Equivalent circuit schematic



### ■ Maximum Ratings and Characteristics

#### ● Absolute Maximum Ratings at T<sub>c</sub>=25°C (unless otherwise specified)

Description	Symbol	Characteristics	Unit	Remarks
Drain-Source Voltage	V <sub>DS</sub>	500	V	
	V <sub>DSDX</sub>	500	V	V <sub>GS</sub> = -30V
Continuous Drain Current	I <sub>D</sub>	±7.5	A	
Pulsed Drain Current	I <sub>DP</sub>	±30	A	
Gate-Source Voltage	V <sub>GS</sub>	±30	V	
Repetitive and Non-Repetitive Maximum Avalanche Current	I <sub>AR</sub>	7.5	A	Note*1
Non-Repetitive Maximum Avalanche Energy	E <sub>AS</sub>	301.1	mJ	Note*2
Repetitive Maximum Avalanche Energy	E <sub>AR</sub>	3.7	mJ	Note*3
Peak Diode Recovery dV/dt	dV/dt	5.9	kV/μs	Note*4
Peak Diode Recovery -di/dt	-di/dt	100	A/μs	Note*5
Maximum Power Dissipation	P <sub>D</sub>	2.02	W	T <sub>a</sub> =25°C
		105		T <sub>c</sub> =25°C
Operating and Storage Temperature range	T <sub>ch</sub>	150	°C	
	T <sub>stg</sub>	-55 to +150	°C	

#### ● Electrical Characteristics at T<sub>c</sub>=25°C (unless otherwise specified)

Description	Symbol	Conditions	min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	500	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	I <sub>D</sub> =250μA, V <sub>DS</sub> =V <sub>GS</sub>	2.5	3.0	3.5	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =500V, V <sub>GS</sub> =0V	-	-	25	μA
		V <sub>DS</sub> =400V, V <sub>GS</sub> =0V	-	-	250	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±30V, V <sub>DS</sub> =0V	-	10	100	nA
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	I <sub>D</sub> =3.8A, V <sub>GS</sub> =10V	-	0.68	0.79	Ω
Forward Transconductance	g <sub>fs</sub>	I <sub>D</sub> =3.8A, V <sub>DS</sub> =25V	4	8	-	S
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V	-	1100	1650	pF
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> =0V	-	100	150	
Reverse Transfer Capacitance	C <sub>rss</sub>	f=1MHz	-	7.5	11	
Turn-On Time	t <sub>d(on)</sub>	V <sub>cc</sub> =300V	-	17	26	ns
	t <sub>r</sub>	V <sub>GS</sub> =10V	-	8.0	12	
Turn-Off Time	t <sub>d(off)</sub>	I <sub>D</sub> =3.8A	-	80	120	
	t <sub>f</sub>	R <sub>GS</sub> =18Ω	-	15	23	
Total Gate Charge	Q <sub>G</sub>	V <sub>cc</sub> =250V	-	35	53	nC
Gate-Source Charge	Q <sub>GS</sub>	I <sub>D</sub> =7.5A	-	9.0	14	
Gate-Drain Charge	Q <sub>GD</sub>	V <sub>GS</sub> =10V	-	10	15	
Avalanche Capability	I <sub>AV</sub>	L=3.93mH, T <sub>ch</sub> =25°C	7.5	-	-	A
Diode Forward On-Voltage	V <sub>SD</sub>	I <sub>F</sub> =7.5A, V <sub>GS</sub> =0V, T <sub>ch</sub> =25°C	-	0.90	1.35	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =7.5A, V <sub>GS</sub> =0V	-	0.35	-	μs
Reverse Recovery Charge	Q <sub>rr</sub>	-di/dt=100A/μs, T <sub>ch</sub> =25°C	-	3.5	-	μC

#### ● Thermal Characteristics

Description	Symbol	Test Conditions	min.	typ.	max.	Unit
Thermal resistance	R <sub>th(ch-c)</sub>	Channel to Case			1.19	°C/W
	R <sub>th(ch-a)</sub>	Channel to Ambient			62.0	°C/W

Note \*1 : T<sub>ch</sub>≤150°C

Note \*2 : Stating T<sub>ch</sub>=25°C, I<sub>AS</sub>=3.0A, L=61.3mH, V<sub>cc</sub>=50V, R<sub>G</sub>=50Ω

E<sub>AS</sub> limited by maximum channel temperature and avalanche current.  
See to 'Avalanche Energy' graph.

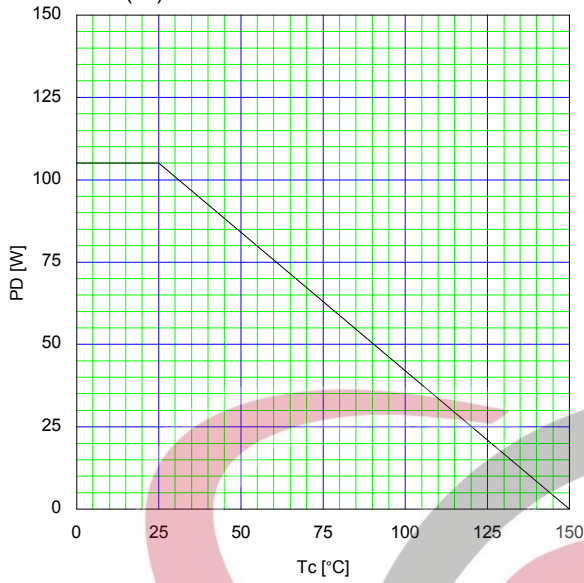
Note \*3 : Repetitive rating : Pulse width limited by maximum channel temperature.

See to the 'Transient Thermal Impedance' graph.

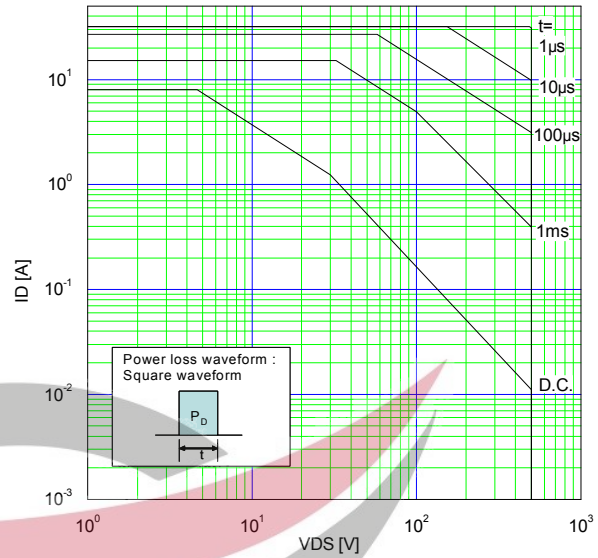
Note \*4 : I<sub>F</sub>≤I<sub>D</sub>, -di/dt=100A/μs, V<sub>cc</sub>≤BV<sub>DSS</sub>, T<sub>ch</sub>≤150°C.

Note \*5 : I<sub>F</sub>≤I<sub>D</sub>, dv/dt=5.9kV/μs, V<sub>cc</sub>≤BV<sub>DSS</sub>, T<sub>ch</sub>≤150°C.

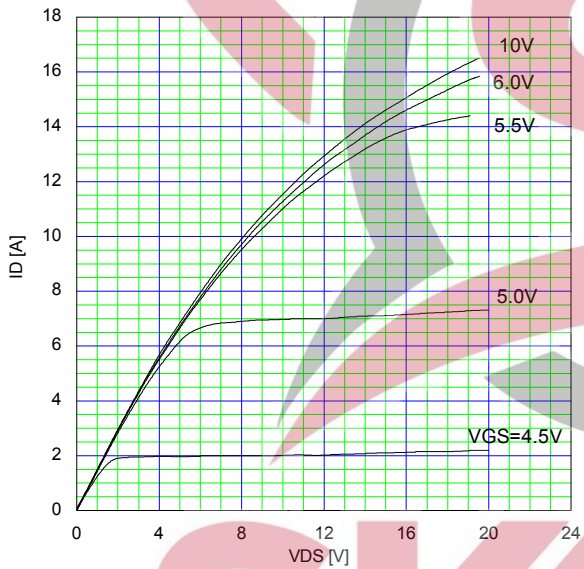
Allowable Power Dissipation  
 $P_D = f(T_c)$



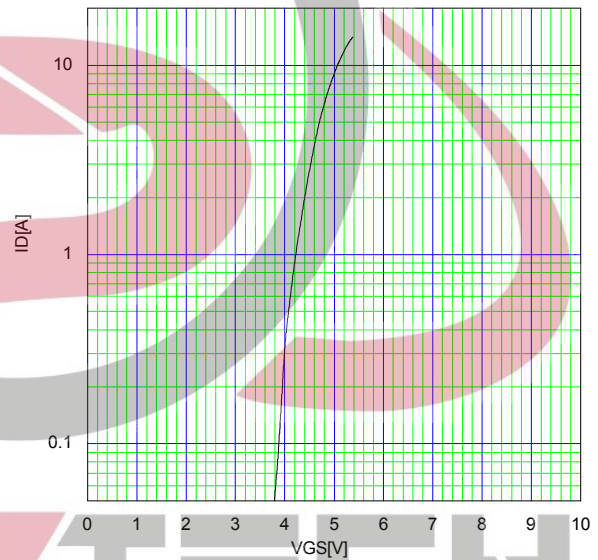
Safe Operating Area  
 $I_D = f(V_{DS})$ ; Duty=0 (Single pulse),  $T_c = 25^\circ\text{C}$



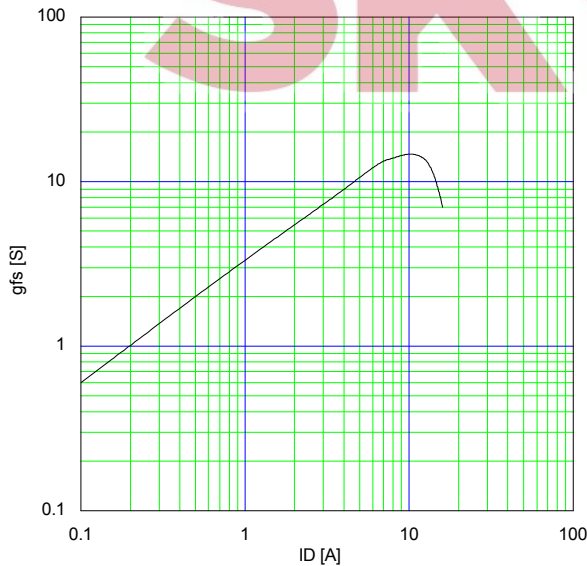
Typical Output Characteristics  
 $I_D = f(V_{DS})$ ; 80 µs pulse test,  $T_{ch} = 25^\circ\text{C}$



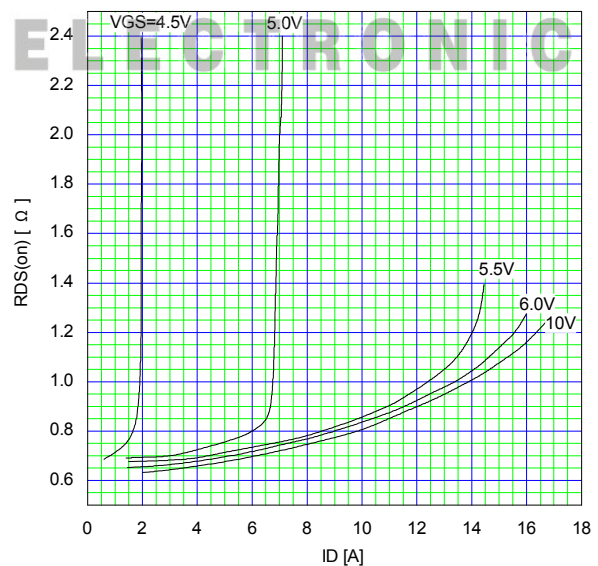
Typical Transfer Characteristic  
 $I_D = f(V_{GS})$ ; 80 µs pulse test,  $V_{DS} = 25\text{V}$ ,  $T_{ch} = 25^\circ\text{C}$



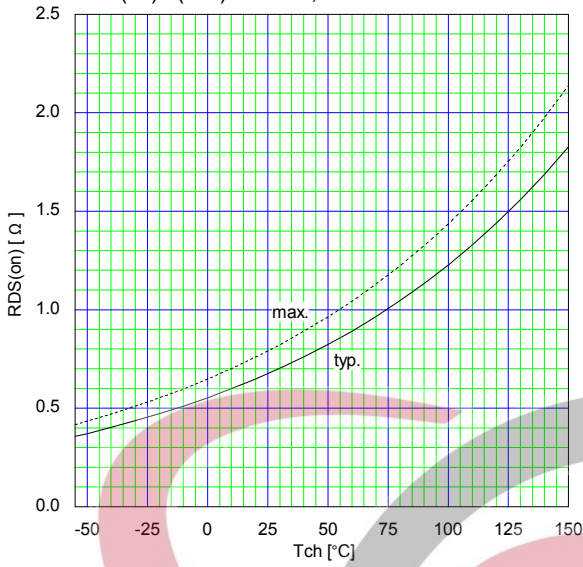
Typical Transconductance  
 $g_{fs} = f(I_D)$ ; 80 µs pulse test,  $V_{DS} = 25\text{V}$ ,  $T_{ch} = 25^\circ\text{C}$



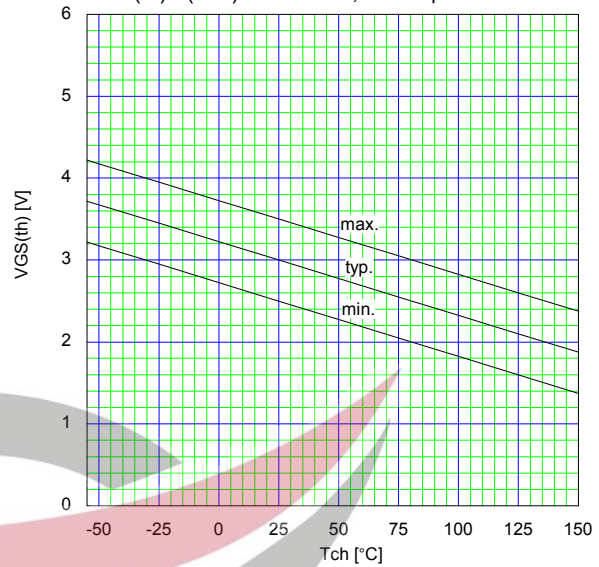
Typical Drain-Source on-state Resistance  
 $R_{DS(on)} = f(I_D)$ ; 80 µs pulse test,  $T_{ch} = 25^\circ\text{C}$



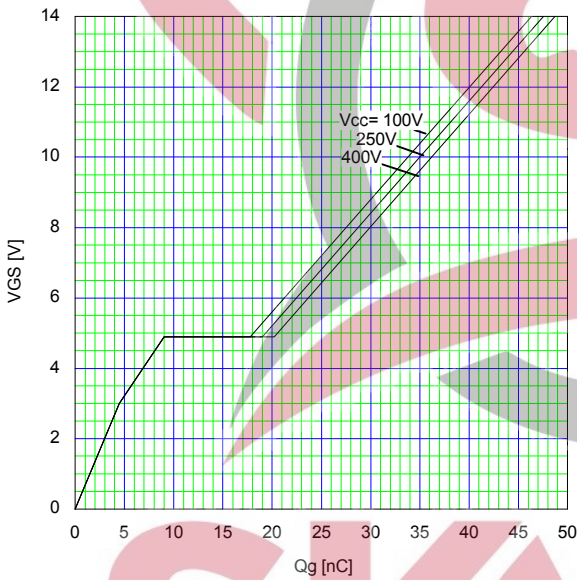
Drain-Source On-state Resistance  
 $R_{DS(on)}=f(T_{ch}):I_D=3.8A, V_{GS}=10V$



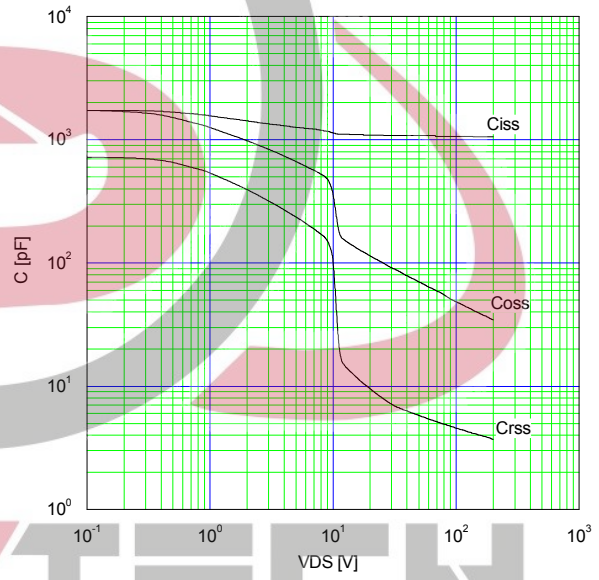
Gate Threshold Voltage vs. T<sub>ch</sub>  
 $V_{GS(th)}=f(T_{ch}):V_{DS}=V_{GS}, I_D=250\mu A$



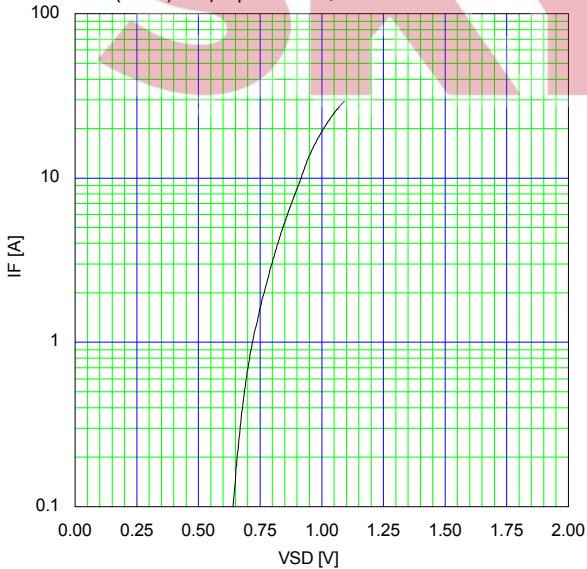
Typical Gate Charge Characteristics  
 $V_{GS}=f(Q_g):I_D=7.5A, T_{ch}=25^\circ C$



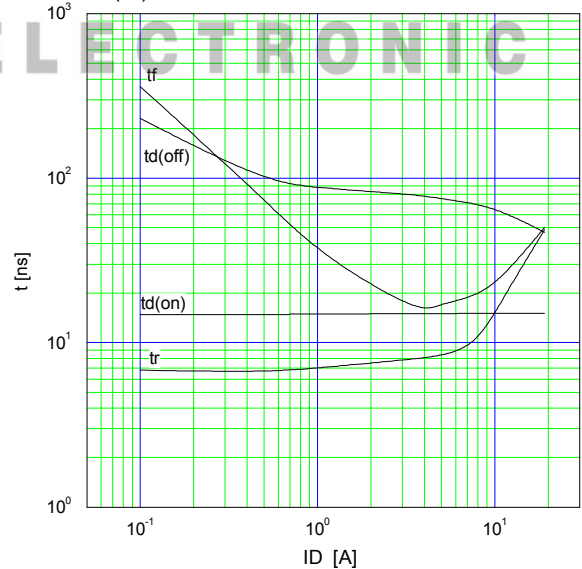
Typical Capacitance  
 $C=f(V_{DS}):V_{GS}=0V, f=1MHz$

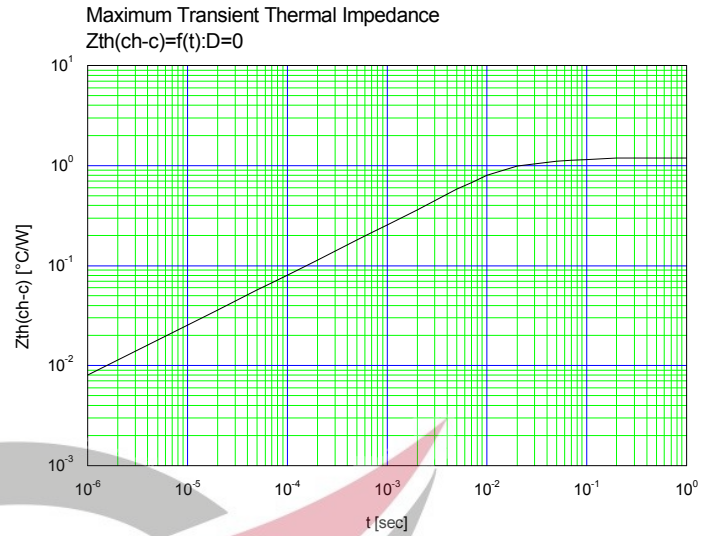
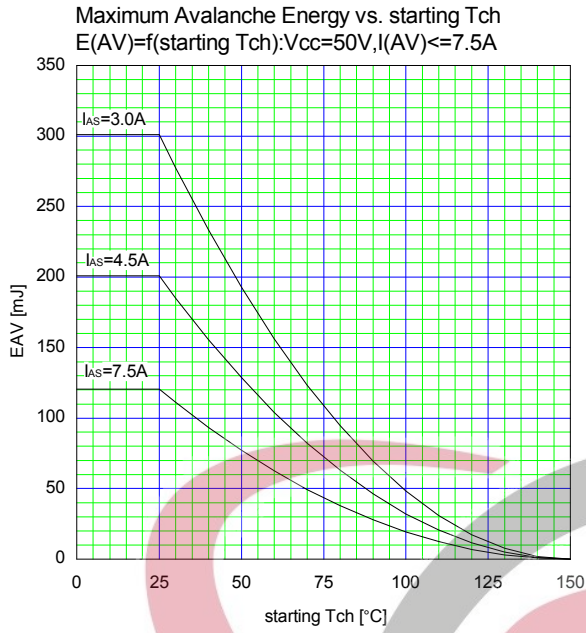


Typical Forward Characteristics of Reverse Diode  
 $I_F=f(V_{SD}):80\mu s \text{ pulse test}, T_{ch}=25^\circ C$



Typical Switching Characteristics vs. ID  
 $t=f(I_D):V_{cc}=300V, V_{GS}=10V, R_G=18\Omega$





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